

## 85 V N-Channel Enhancement Mode MOSFET

### 1. Product Information

#### 1.1 Features

- ◇ Surface-mounted package
- ◇ MSL1
- ◇ Tj max 175°C
- ◇ Advanced SGT cell design

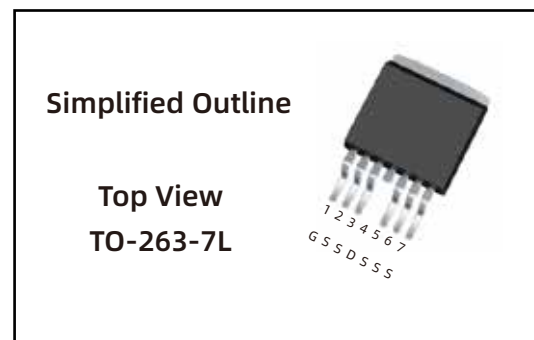
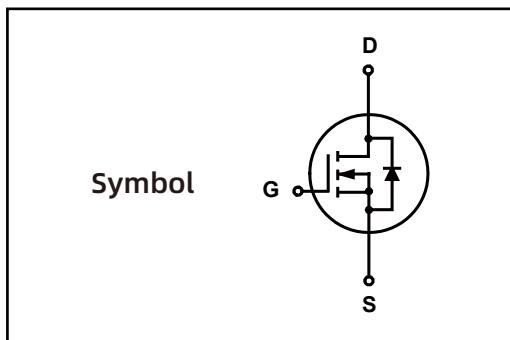
#### 1.2 Applications

- ◇ E- Tool appliances
- ◇ BMS appliances
- ◇ High power inverter system
- ◇ Inverter appliances

#### 1.3 Quick reference

- ◇  $BV \cong 85\text{ V}$
- ◇  $P_{\text{tot}} \cong 250\text{ W}$
- ◇  $I_D \cong 280\text{ A}$
- ◇  $R_{\text{DS(ON)}} \cong 2.0\text{ m}\Omega @ V_{\text{GS}} = 10\text{ V}$

### 2. Pin Description



### 3. Marking Information

Product Name	Marking
LN018N085D	LN018N085D AYWWZZ XXXXXX

## 4.Limiting Values

$V_{DS}$	Drain-Source Voltage	$T_C = 25\text{ }^\circ\text{C}$	85	-	V
$V_{GS}$	Gate-Source Voltage	$T_C = 25\text{ }^\circ\text{C}$	-	$\pm 20$	V
$I_D^{***}$	Drain Current ( DC )	$T_C = 25\text{ }^\circ\text{C}, V_{GS} = 10\text{ V}$	-	280	A
		$T_C = 100\text{ }^\circ\text{C}, V_{GS} = 10\text{ V}$	-	186	A
$I_{DM}^{*,***}$	Drain Current ( Pulsed )	$T_C = 25\text{ }^\circ\text{C}, V_{GS} = 10\text{ V}$	-	1000	A
$P_{tot}$	Drain power dissipation	$T_C = 25\text{ }^\circ\text{C}$	-	227	W
$T_{stg}$	Storage Temperature		-55	175	$^\circ\text{C}$
$T_J$	Junction Temperature		-	175	$^\circ\text{C}$
$I_S$	Continuous-Source Current	$T_C = 25\text{ }^\circ\text{C}$	-	280	A
$E_{AS}$	Single Pulsed Avalanche Energy	$V_{DD} = 40\text{ V}, L = 0.1\text{ mH}$	-	1605	mJ
$R_{\theta JA}^{**}$	Thermal Resistance- Junction to Ambient		-	40	$^\circ\text{C/W}$
$R_{\theta JC}^{**}$	Thermal Resistance- Junction to Case		-	0.55	

Notes :

\* Pulse width  $\leq 300\mu\text{s}$ , duty cycle  $\leq 2\%$

\*\* Surface Mounted on minimum footprint pad area.

\*\*\* Limited by bonding wire

## 5.Ordering Code

Product Name	Package	Reel Size	Tape width	Quantity	Note
LN018N085D	TO263-7L			800	

Note: COMTECH defines " Green " as lead-free ( RoHS compliant ) and halogen free ( Br or Cl does not exceed 900 ppm by weight in homogeneous material and total of Br and Cl does not exceed 1500 ppm by weight; Follow IEC 61249-2-21 and IPC / JEDEC J-STD-020C )

## 6. Electrical Characteristics (TA=25 ° Unless Otherwise Noted )

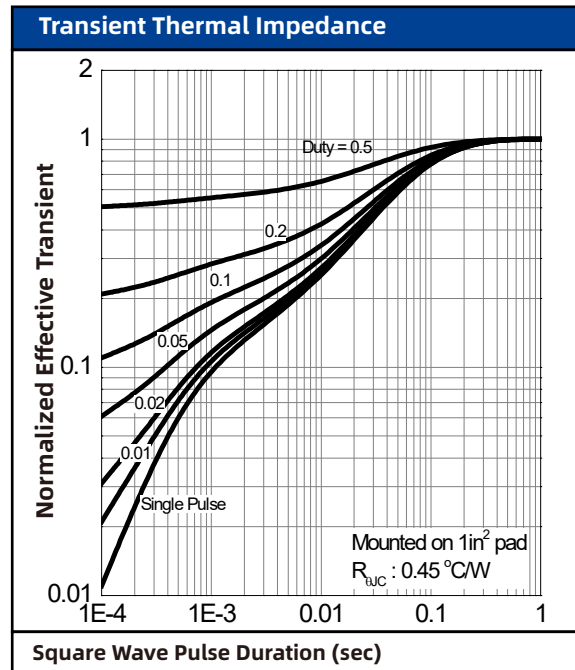
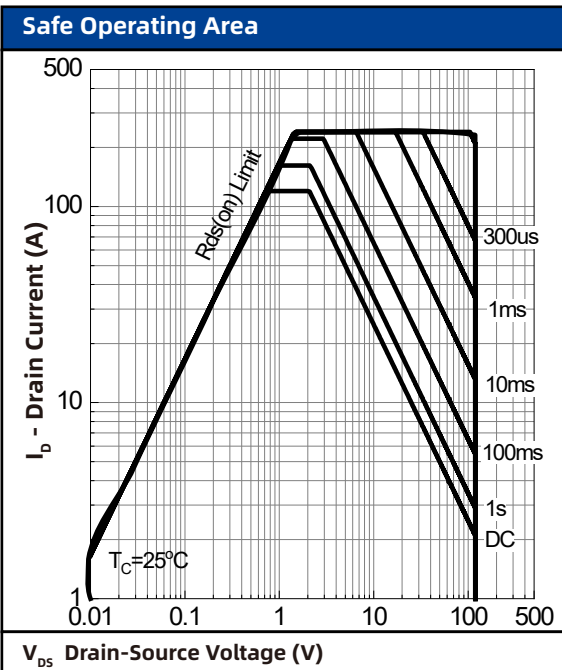
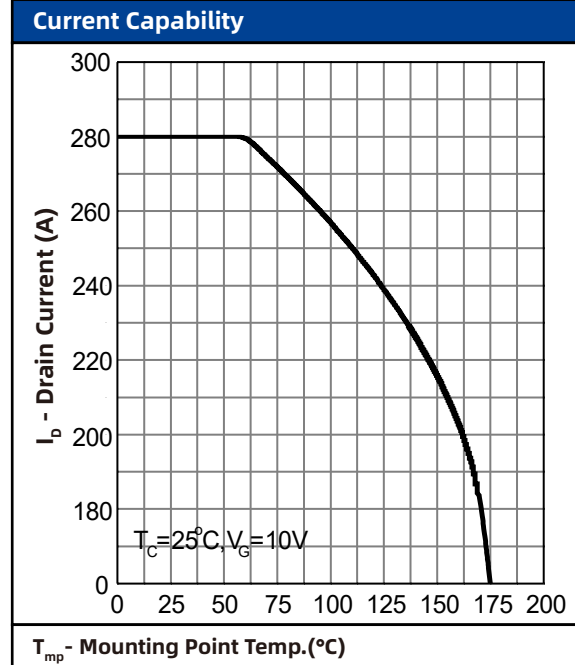
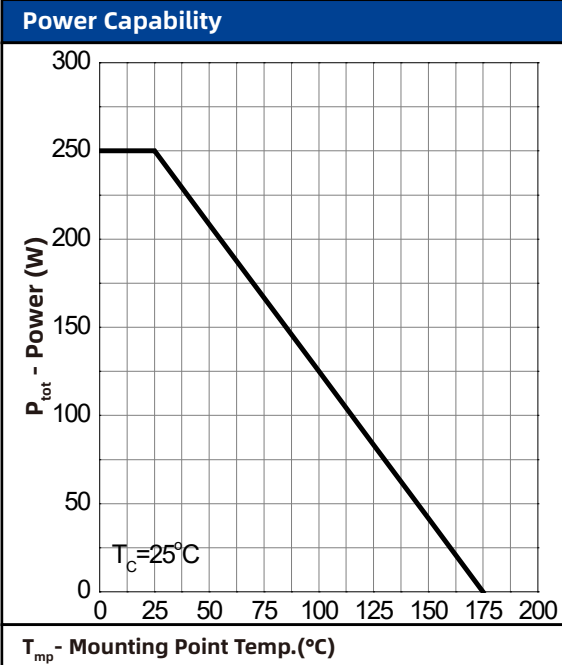
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Static Characteristics</b>						
$BV_{DSS}$	Drain-Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_{DS} = 250\ \mu\text{A}$	85	95	-	V
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{DS} = 250\ \mu\text{A}$	2	-	4	V
$I_{DSS}$	Drain Leakage Current	$V_{DS} = 85\text{V}, V_{GS} = 0\text{ V}$	-	-	1	$\mu\text{A}$
		$T_j = 85\text{ }^\circ\text{C}$	-	-	30	$\mu\text{A}$
$I_{GSS}$	Gate Leakage Current	$V_{GS} = 0\text{ V}, V_{DS} = \pm 20\text{ V}$	-	-	$\pm 100$	nA
$R_{DS(ON)}^a$	On-State Resistance	$V_{GS} = 10\text{ V}, I_{DS} = 30\text{ A}$	-	1.8	2.0	m $\Omega$
<b>Diode Characteristics</b>						
$V_{SD}^a$	Diode Forward Voltage	$I_{SD} = 30\text{ A}, V_{GS} = 0\text{ V}$	-	-	1.2	V
$t_{rr}$	Reverse Recovery Time	$I_{DS} = 30\text{ A}, V_{GS} = 0\text{ V}$	-	78	-	nS
$Q_{rr}$	Reverse Recovery Charge	$dI_{SD}/dt = 100\text{ A}/\mu\text{s}$	-	110	-	nC
<b>Dynamic Characteristics<sup>b</sup></b>						
$C_{ISS}$	Input Capacitance	$V_{GS} = 0\text{ V}, V_{DS} = 40\text{ V}$ Frequency = 1 MHz	-	7234	-	pF
$C_{OSS}$	Output Capacitance		-	1280	-	
$C_{rSS}$	Reverse Transfer Capacitance		-	99	-	
$t_d(on)$	Turn-on Delay Time	$V_{DS} = 40\text{ V}, V_{GEN} = 10\text{ V},$ $R_G = 4.5\ \Omega, R_L = 1.3\ \Omega,$ $I_{DS} = 30\text{ A}$	-	41	-	nS
$t_r$	Turn-on Rise Time		-	68	-	
$t_d(off)$	Turn-off Delay Time		-	76	-	
$t_f$	Turn-off Fall Time		-	44	-	
<b>Gate Charge Characteristics<sup>b</sup></b>						
$Q_g$	Total Gate Charge	$V_{DS} = 40\text{ V}, V_{GS} = 10\text{ V},$ $I_{DS} = 30\text{ A}$	-	124	-	nC
$Q_{gs}$	Gate-Source Charge		-	31.2	-	
$Q_{gd}$	Gate-Drain Charge		-	39.2	-	

Notes :

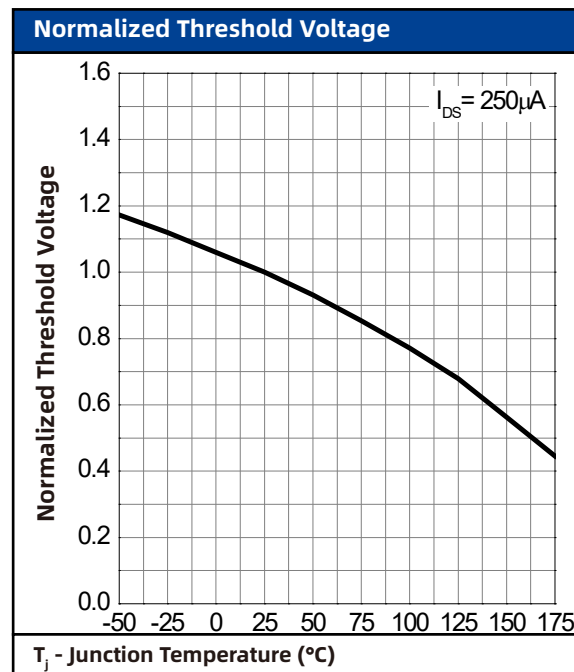
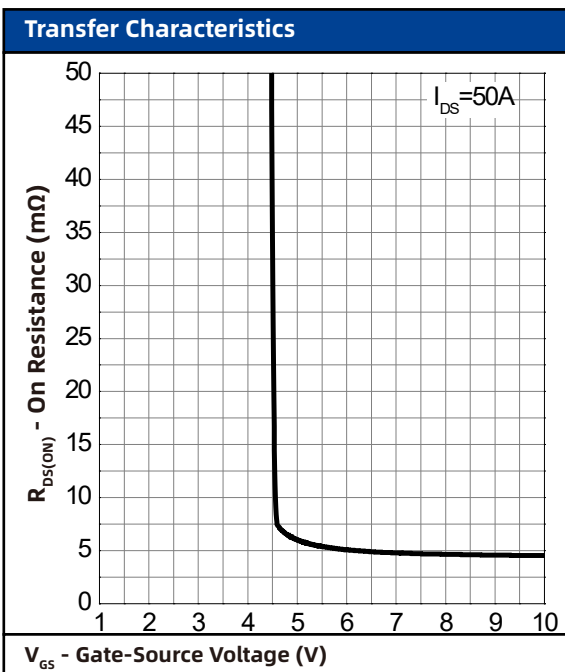
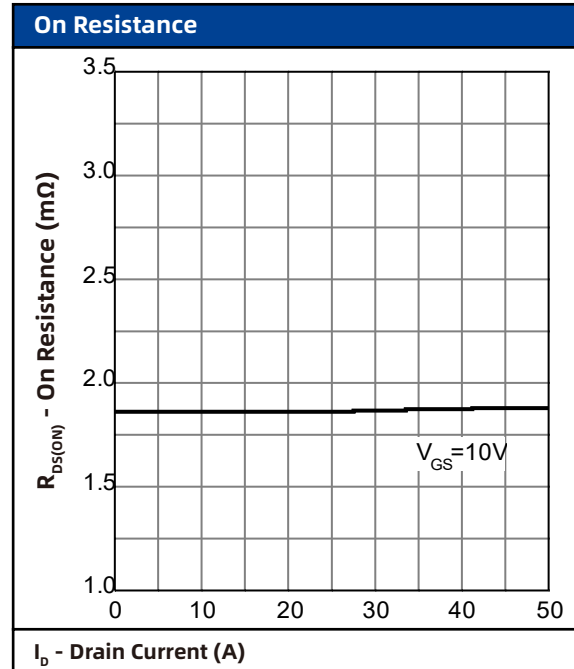
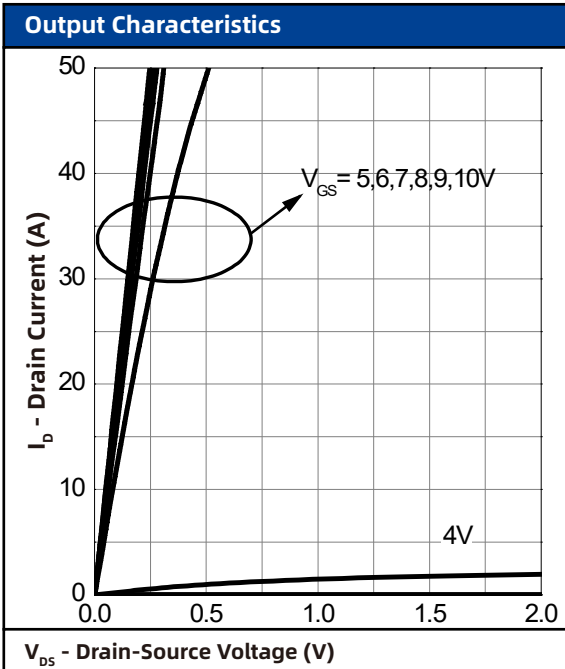
a : Pulse test ; pulse width  $\leq 300\ \mu\text{s}$ , duty cycle  $\leq 2\%$

b : Guaranteed by design, not subject to production testing

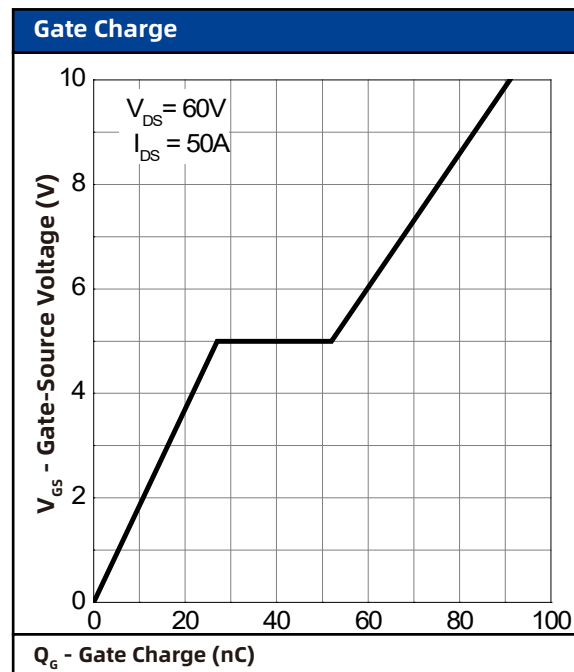
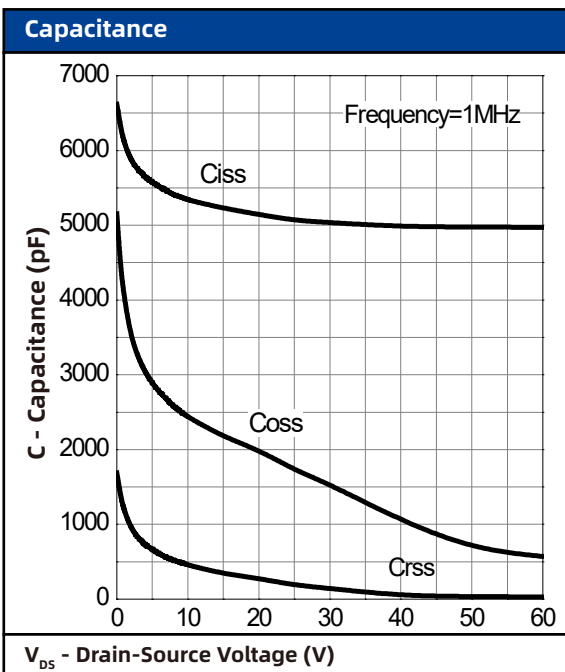
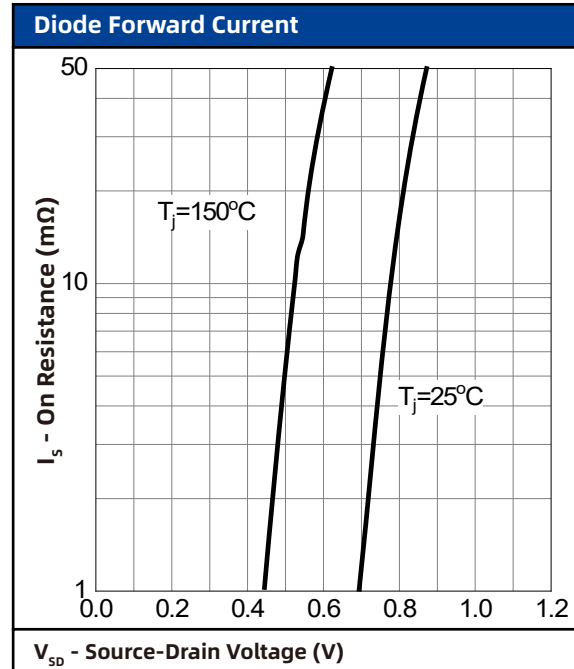
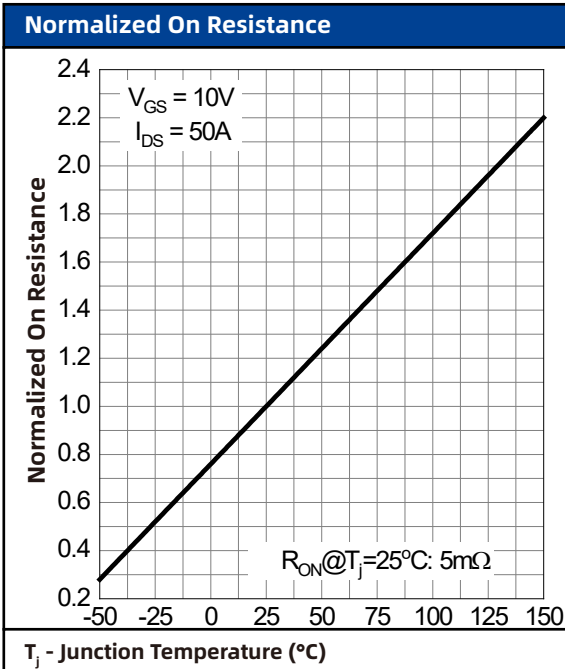
## 7. Typical Characteristics



## 7. Typical Characteristics (cont.)

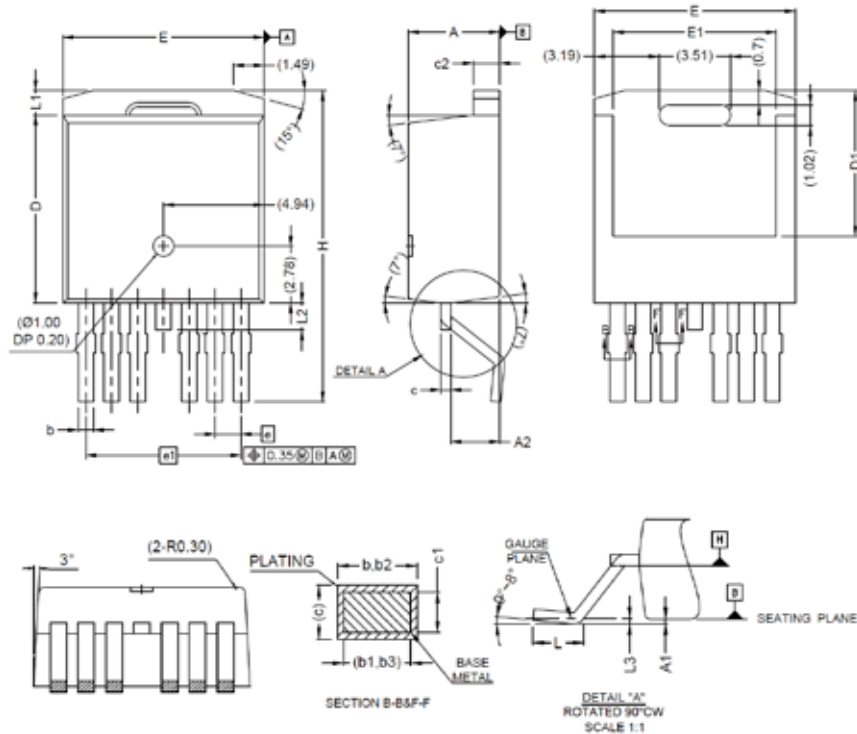


## 7. Typical Characteristics (cont.)



## 8. Package Dimensions

### TO-263-7L Package



Symbol	Dimensions In Millimeters	
	Min	Max
A	4.30	4.70
A1	-	0.25
A2	2.20	2.60
b	0.65	0.85
b1	0.65	0.80
b2	0.80	1.00
b3	0.80	0.95
c	0.45	0.60
c1	0.45	0.55
c2	1.25	1.40
D	9.00	9.40
D1	6.86	7.42
E	9.68	10.08
E1	7.70	8.30
e	1.27 BSC	
e1	7.62 BSC	
L	1.78	2.79
L1	-	1.60
L2	-	1.78
L3	0.25BSD	
H	14.61	15.88